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View Online at https://aerobasegroup.com/nsn/5961-01-172-9920 **Inclosure Material:** Metal **Overall Length:** 1.573 inches **Overall Height:** 0.450 inches **Overall Width:** 1.050 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Collector **Internal Junction Configuration:** Npn **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 140.0 breakdown voltage, collector-to-base, emitter open and 6.0 emitter to base voltage, static, collector open and 120.0 breakdown voltage, collector-to-emitter, base open **Current Rating Per Characteristic:** 25.00 amperes source cutoff current and 10.00 amperes source cutoff current **Power Rating Per Characteristic:** 200.0 watts small-signal input power, common-collector **Transfer Ratio:** 80.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Terminal Type And Quantity:** 2 pin and 1 case **Specification Data:** 80131-release6456 professional/industrial association specification

N/a

Shelf Life:

Unit Of Measure:

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No

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